



# 《风光欣》技术资料

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## A1015

PNP EPITAXIAL SILICON TRANSISTOR

LOW FREQUENCY AMPLIFIER

HIGH FREQUENCY OSC

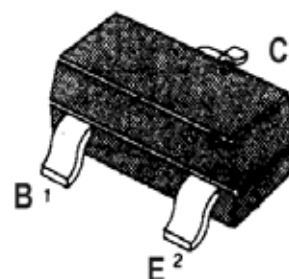
\*Complement to **C1815**

\*Collector-Base Voltage  $V_{CBO} = -50V$

### ABSOLUTE MAXIMUM RATINGS( $T_A = 25$ )

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	$V_{CBO}$	-50	V
Collector-Emitter Voltage	$V_{CEO}$	-50	V
Emitter -Base Voltage	$V_{EBO}$	-5	V
Collector Current	$I_C$	-150	mA
Base Current	$I_B$	-50	mA
Collector Dissipation	$P_C$	400	mW
Junction Temperature	$T_J$	125	
Storage Temperature	$T_{STG}$	-55 ~150	

SOT-23



### ELECTRICAL CHARACTERISTICS( $T_A = 25$ )

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	$BV_{CBO}$	$I_C = -100 \mu A, I_E = 0$	-50			V
Collector- Emitter Breakdown Voltage	$BV_{CEO}$	$I_C = -10mA, I_B = 0$	-50			V
Emitter -Base Breakdown Voltage	$BV_{EBO}$	$I_E = -10 \mu A, I_C = 0$	-5			V
Collector-Cut-off Current	$I_{CBO}$	$V_{CB} = -50V, I_E = 0$			-0.1	$\mu A$
Emitter-Cut-off Current	$I_{EBO}$	$V_{EB} = -5V, I_C = 0$			-0.1	$\mu A$
DC Current Gain	$h_{FE1}$	$V_{CE} = -6V, I_C = -2mA$	70		400	
	$h_{FE2}$	$V_{CE} = -6V, I_C = -150mA$	25			
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -100mA, I_B = -10mA$		-0.1	-0.3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = -100mA, I_B = -10mA$			-1.1	V
Current Gain-Bandwidth Product	$f_T$	$V_{CE} = -10V, I_C = 1mA$	80			MHZ
Output Capacitance	$C_{OB f=1MHZ}$	$V_{CB} = -10V, I_E = 0,$		4.0	7.0	pF
Noise Figure	NF	$V_{CE} = -6V, I_C = -0.1mA$		1.0	10.0	dB
		$F = 100HZ, R_G = 10K$				

### Hfe CLASSIFICATION

Classification	O	Y	GR
HFE(1)	70-140	120-240	200-400